

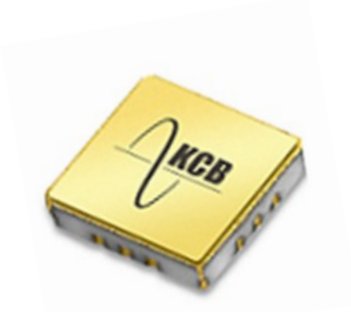
KCB822

High Isolation SPDT
0.02 – 6 GHz

DESCRIPTION

KCB822 is a GaAs pHEMT Non-Reflective high performance, low loss switch in a 3x3 mm leadless Hermetic Surface-Mount Technology (SMT) package for Harsh Environments including Defense and Satellite application. This device can be ordered with the 100% screening requirements of MIL-PRF-38535 Class B and S, in addition to the required QCI.

FEATURES

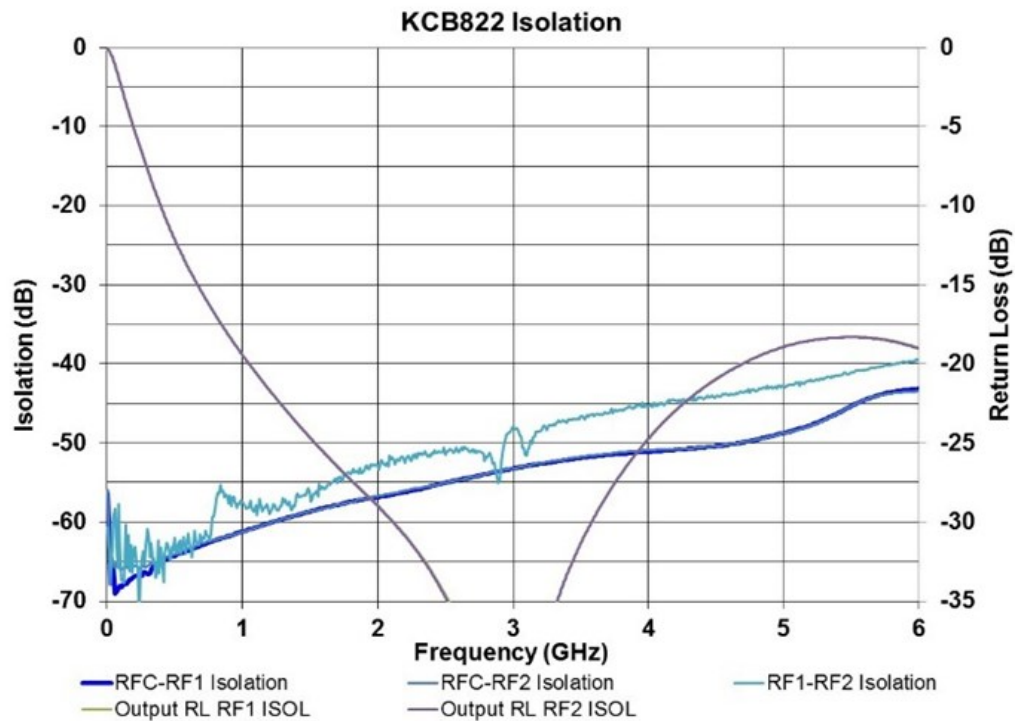
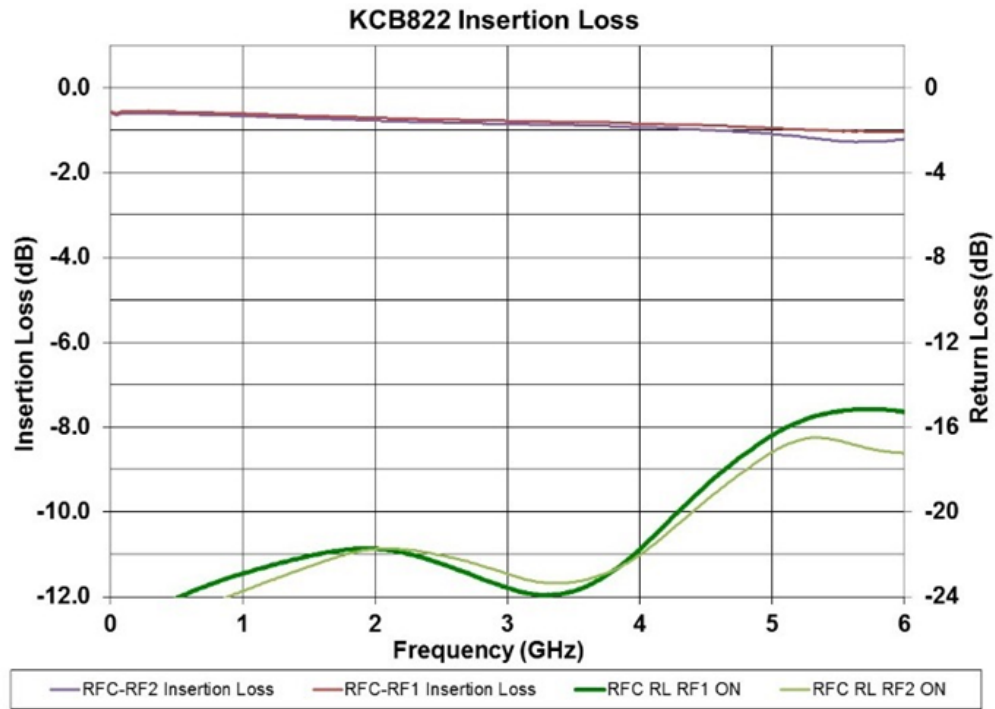


- ✓ **Low Loss: .8 dB @ 2 GHz Isolation: 55 dB @ 2 GHz.**
- ✓ **Non Reflective Match in off state (S22).**
- ✓ **NASA EEE-INST-002 compliant.**
- ✓ **Successfully Tested to 1M RAD TID.**
- ✓ **High Reliability Class B and S Screening Available.**
- ✓ **See Page 4 for MFR HI –REL Ordering Details.**

ELECTRICAL CHARACTERISTICS (+25°C)

| Parameter | Conditions | Min | Typical | Max | Units |
|--|--|-------------|-------------|-------------|-------|
| Insertion Loss | 0.02 – 2.0 GHz | | 0.75 | 1.10 | dB |
| | 2.0 – 3.0 GHz | | 0.8 | 1.25 | dB |
| | 3.0 – 4.0 GHz | | 1.0 | 1.35 | dB |
| | 4.0 – 6.0 GHz | | 1.5 | 1.8 | dB |
| RF1/RF2 Return Loss (ON-State) | 0.02 – 2.0 GHz | 19 | 22 | | dB |
| | 2.0 – 3.0 GHz | 15 | 22 | | dB |
| | 3.0 – 4.0 GHz | 12 | 18 | | dB |
| | 4.0 – 6.0 GHz | 9 | 12 | | dB |
| RF1/RF2 Return Loss (OFF-State) | 0.02 – 0.1 GHz | 0 | 0 | | dB |
| | 0.1 – 0.5 GHz | 5 | 8 | | dB |
| | 0.5 – 2.0 GHz | 9 | 11 | | dB |
| | 2.0 – 3.0 GHz | 12 | 15 | | dB |
| | 3.0 – 4.0 GHz | 12 | 15 | | dB |
| | 4.0 – 6.0 GHz | 9 | 13 | | dB |
| Isolation | 0.02 – 2.0 GHz | 50 | 55 | | dB |
| | 2.0 – 3.0 GHz | 50 | 55 | | dB |
| | 3.0 – 4.0 GHz | 45 | 50 | | dB |
| | 4.0 – 6.0 GHz | 40 | 45 | | dB |
| Input 1 dB Compression (P1dB) | Vctrl = 0V/+5V, 0.5- 2.0 GHz | | +30 | | dBm |
| | .02 -.50 Ghz | | +24 | | dBm |
| Third Order Output Intercept Point (IP3) | +8 dBm Input Tones ,1 MHz Spacing, Vctrl = 0V/5V, 0.5- 2.0 GHz | | +46 | | dBm |
| | .02 - 0.5 Ghz | | +30 | | dBm |
| Switching Speed: Rise, Fall ON/OFF | 10/90% or 90/10% RF | | 5 | | nS |
| | 50% CTL to 90/10% RF | | 15 | | nS |
| Negative (Positive) Control Vctrl High Vctrl Low I ctrl | DC Voltage | -7.0 (+2.7) | -5.0 (+5.0) | -4.5 (+7.0) | V |
| | DC Voltage | -0.25 | 0 | +0.25 | V |
| | DC Current | | 50 | 200 | uA |

TYPICAL PERFORMANCE (+25°C)



Note: Typical Insertion loss change .003db/degree C. .

TRUTH TABLE/NEGATIVE CONTROL

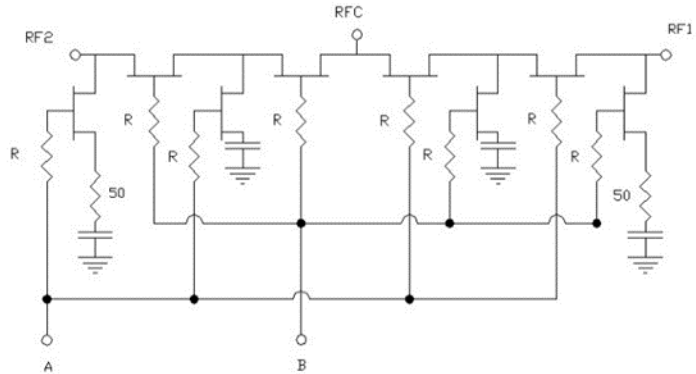
| Control Input | | Signal Path State | |
|---------------|----|-------------------|------------|
| B | A | RFC to RF1 | RFC to RF2 |
| -5.0 | 0 | ON | OFF |
| 0 | -5 | OFF | ON |

TRUTH TABLE/POSITIVE CONTROL

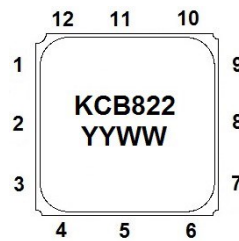
| Control Input | | Signal Path State | |
|---------------|------|-------------------|------------|
| B | A | RFC to RF1 | RFC to RF2 |
| 0 | +5.0 | ON | OFF |
| +5.0 | 0 | OFF | ON |

Note: External blocking capacitors are required on all RF ports. Capacitor should be selected to allow for low frequency operation.

SCHEMATIC



PINOUT



XXX = Serial # will be added for Class B and S Part #

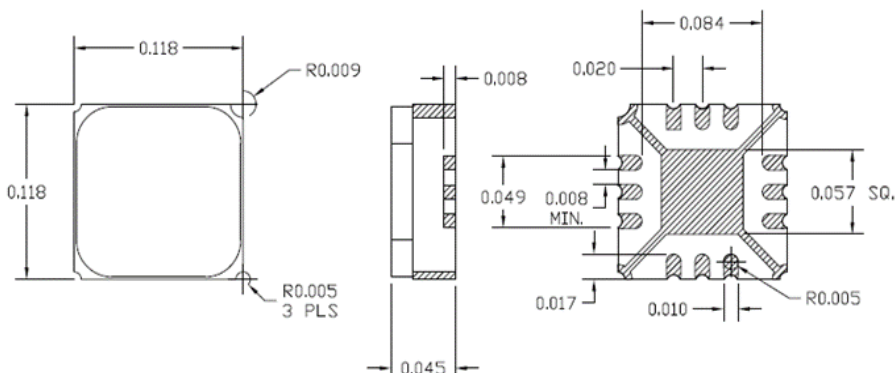
| | |
|----|-----|
| 1 | GND |
| 2 | RF1 |
| 3 | GND |
| 4 | GND |
| 5 | GND |
| 6 | GND |
| 7 | GND |
| 8 | RF2 |
| 9 | B |
| 10 | A |
| 11 | RFC |
| 12 | GND |

ABSOLUTE MAXIMUM RATINGS

Exceeding Max limits may cause damage

| Characteristic | Min. | Max. | Units |
|-----------------------|------|------|-------|
| Control Voltage (A+B) | -0.2 | +9.0 | Volts |
| RF Input Power | | +30 | dBm |
| Storage Temperature | -65 | +150 | °C |
| Operating Case Temp | -55 | +125 | °C |
| Junction Temperature | | +175 | °C |

OUTLINE DRAWING



Electrostatic Sensitive Device. Proper ESD precaution should be used when handling device.



MFR HI-REL SCREENING FLOW

| Test Inspection | MIL – STD -883 | | Requirement | |
|---------------------------|---------------------------|--------------------------|----------------------|-----------------------|
| | Method | Condition | Class B | Class S |
| Wafer Lot Acceptance /1 | 5007 | | N/A | Per Wafer Lot |
| Non-Destructive Bond Pull | 2023 | | SPC | SPC |
| Internal Visual | 2010 | A= Class S, B = Class B | 100% | 100% |
| Temperature Cycle | 1010 | C | 100% | 100% |
| Acceleration | 2001 | E (Y1 only) | 100% | 100% |
| PIND | 2020 | A (5 Cycles) | N/A | 100% |
| Serialization | Per Product Specification | | 100% | 100% |
| Radiographic | 2012 | 2 views | N/A | 100% |
| Electrical Test | Small Signal Testing | +25°C | 100% | 100% |
| Burn In | 1015 | A | 100%/160 Hours/125°C | 100%/320 Hours/125 °C |
| Final Electrical | Small Signal Testing | +25°C | 100% | 100% |
| PDA Calculation | 5004 | 25% Δ IL / 100% Δ Icc | 5% | 5%/3% functional |
| Group A Electrical /5 | Per Product Specification | -55°C + 125°C | 45/0 | 45/0 |
| Leak Test | 1014 A and C | 1 x 10 ⁻⁸ Max | 100% | 100% |
| External Visual | 2009 | | 100% | 100% |

NOTES

1. Product under configuration control per KCB QAP 015.
2. Customer will be notified of all class 1 changes for Class B and S part numbers.
3. Wafer Lot Acceptance will include 100% die visual, SEM analysis and Lot Traceability.
4. Electrical Test Data will be recorded for each Serial number and included in Final Test Report for all Class S part number.
5. Group A Electrical testing will include the Small Signal and Ic at the Min/Max operating condition. The Dynamic test (P1dB, IP3, SS) will be tested at +25c only.

ORDERING INFORMATION

| | Unscreened | Class B | Class S |
|---------------------------|------------|---------|---------|
| KCB Solutions Part Number | KCB822C | KCB822B | KCB822S |

